JSR i-Line Negative Type Photoresist for Thick Film Application

- Rectangular profile
- Easily striped by organic solvent
- High thermal stability

Process Conditions
- Substrate: Bare Si
- Exposure: Nikon NSR2005i9C
- Illumination: NA0.57, φ0.60

Pattern Profiles

<table>
<thead>
<tr>
<th>Focus</th>
<th>FT = 6.00 μm</th>
<th>FT = 3.00 μm</th>
</tr>
</thead>
<tbody>
<tr>
<td>- 0.40 μm</td>
<td>2.00 μm-1L1S</td>
<td>1.00 μm-1L1S</td>
</tr>
<tr>
<td>+/- 0.00 μm</td>
<td></td>
<td></td>
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<tr>
<td>+ 0.40 μm</td>
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</tbody>
</table>

JSR KrF Photoresist for Implant Layer

180 nm Space on FinFET Topography

Process Conditions
- Substrate: 22 nm node SRAM topography
- Resist FT: 230 nm
- Exposure: ASML 750E
- Illumination: NA0.60, φ0.45
- Exposure Courtesy of imec

180 nm Patterns on SiO₂

Process Conditions
- Substrate: SiO₂ (100 nm)
- Resist FT: 200 nm
- Exposure: Nikon NSR S203B
- Illumination: NA0.68, φ0.75